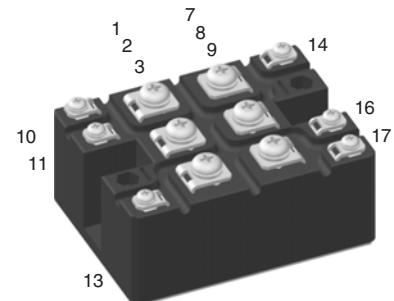
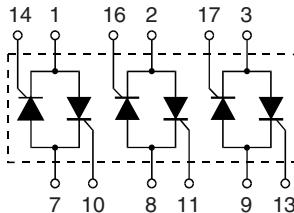


Three Phase AC Controller Modules

I_{RMS} = 80/95 A
V_{RRM} = 1200/1400 V

Preliminary data

V _{RSM}	V _{RRM}	Type
V _{DSM}	V _{DRM}	
V	V	
1200	1200	VWO 80-12io7
1400	1400	VWO 80-14io7
		VWO 95-12io7
		VWO 95-14io7



Symbol	Conditions	Maximum Ratings		
		VWO 80	VWO 95	
I _{RMS}	T _C = 85°C, 50 - 400 Hz (per phase)	82	96	A
I _{TRMS}	T _{VJ} = T _{VJM}	59	69	A
I _{TAVM}	T _C = 85°C; (180° sine)	37	44	A
I _{TSM}	T _{VJ} = 45°C; t = 10 ms (50 Hz), sine V _R = 0 t = 8.3 ms (60 Hz), sine	1000 1100	1150 1230	A
	T _{VJ} = T _{VJM} t = 10 ms (50 Hz), sine V _R = 0 t = 8.3 ms (60 Hz), sine	900 1000	1000 1100	A
I ² t	T _{VJ} = 45°C t = 10 ms (50 Hz), sine V _R = 0 t = 8.3 ms (60 Hz), sine	5000 5080	6600 6280	A ² s
	T _{VJ} = T _{VJM} t = 10 ms (50 Hz), sine V _R = 0 t = 8.3 ms (60 Hz), sine	4050 4200	5000 5080	A ² s
(di/dt) _{cr}	T _{VJ} = T _{VJM} repetitive, I _T = 150 A f = 50 Hz, t _p = 200 μs V _D = 2/3 V _{DRM}	100	100	A/μs
	I _G = 0.3 A non repetitive, I _T = I _{TAVM} di _G /dt = 0.3 A/μs		500	A/μs
(dv/dt) _{cr}	T _{VJ} = T _{VJM} ; V _{DR} = 2/3 V _{DRM} R _{GR} = ∞; method 1 (linear voltage rise)	1000	1000	V/μs
P _{GM}	T _{VJ} = T _{VJM} t _p = 30 μs I _T = I _{TAVM} t _p = 300 μs	10 5	W	
P _{GAVM}		0.5	W	
V _{RGM}		10	V	
T _{VJ}		-40...+125	°C	
T _{VJM}		125	°C	
T _{stg}		-40...+125	°C	
V _{ISOL}	50/60 Hz, RMS t = 1 min	2500	V~	
	I _{ISOL} ≤ 1 mA t = 1 s	3000	V~	
M _d	Mounting torque (M5) Terminal connection torque (M3; M5)	5/44±15 % 1.5/13±15 %	Nm/lb.in.	
Weight	typ.	250	g	

Data according to IEC 60747 refer to a single thyristor/diode unless otherwise stated.

Symbol	Conditions	Characteristic Values		
		VWO 80	VWO 95	
I_D, I_R	$T_{VJ} = T_{VJM}; V_R = V_{RRM}; V_D = V_{DRM}$	\leq	5	5 mA
V_T	$I_T = 150 \text{ A}; T_{VJ} = 25^\circ\text{C}$	\leq	1.65	1.57 V
V_{T0}	For power-loss calculations only		0.85	0.85 V
r_T			5.2	4.8 mΩ
V_{GT}	$V_D = 6 \text{ V}; T_{VJ} = 25^\circ\text{C}$	\leq	1.0	1.0 V
	$T_{VJ} = -40^\circ\text{C}$	\leq	1.6	1.6 V
I_{GT}	$V_D = 6 \text{ V}; T_{VJ} = 25^\circ\text{C}$	\leq	100	100 mA
	$T_{VJ} = -40^\circ\text{C}$	\leq	150	150 mA
V_{GD}	$T_{VJ} = T_{VJM}; V_D = 2/3 V_{DRM}$	\leq	0.2	0.2 V
I_{GD}		\leq	5	5 mA
I_L	$T_{VJ} = 25^\circ\text{C}; t_p = 10 \mu\text{s}$	\leq	200	200 mA
	$I_G = 0.3 \text{ A}; di_G/dt = 0.3 \text{ A}/\mu\text{s}$			
I_H	$T_{VJ} = 25^\circ\text{C}; V_D = 6 \text{ V}; R_{GK} = \infty$	\leq	150	150 mA
t_{gd}	$T_{VJ} = 25^\circ\text{C}; V_D = 1/2 V_{DRM}$	\leq	2	2 μs
	$I_G = 0.3 \text{ A}; di_G/dt = 0.3 \text{ A}/\mu\text{s}$			
t_q	$T_{VJ} = T_{VJM}; I_T = 20 \text{ A}, t_p = 200 \mu\text{s};$ $di/dt = -10 \text{ A}/\mu\text{s}$ $V_R = 100 \text{ V}; dv/dt = 15 \text{ V}/\mu\text{s}; V_D = 2/3 V_{DRM}$	typ.	150	150 μs
R_{thJC}	per thyristor; sine 180°el		0.81	0.66 K/W
	per module		0.135	0.11 K/W
R_{thJK}	per thyristor; sine 180°el		1.0	0.93 K/W
	per module		0.167	0.155 K/W
d_s	Creeping distance on surface		8.0	mm
d_A	Creepage distance in air		4.5	mm
a	Max. allowable acceleration		50	m/s ²

Dimensions in mm (1 mm = 0.0394")

